2SD288 NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

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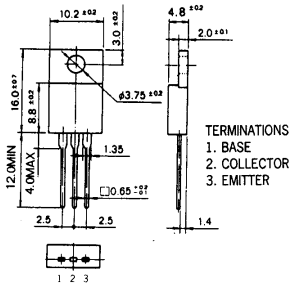
TO-220



ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	8 0	V
Collector-Emitter Voltage	V_{CEO}	55	V
Emitter-Base voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	3	A
Collector Dissipation (Tc=25°C)	P_C	20	W
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	-50~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}= 50V , I_E=0			50	µA
DC Current Gain	h_{FE1}	V_{CE}= 5V , I_C=0.5A	40		240	
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1A , I_B=0.1A			1.0	V
Current Gain Bandwidth Product						